2.5V Drive Nch MOS FET **RTR020N05**

Structure

Silicon N-channel MOS FET

Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT3).
- 3) Low voltage drive (2.5V drive).

Applications

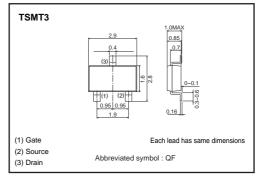
Switching

Packaging specifications and hre

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RTR020N05	0		

•External dimensions (Unit : mm)

Inner circuit



(3) (1)0 (1) Gate (2) Source (3) Drain (2)*1 ESD PROTECTION DIODE *2 BODY DIODE

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	45	V
Gate-source voltage		Vgss	12	V
Ducin comment	Continuous	ID	±2.0	А
Drain current	Pulsed	I _{DP} *1	±8	А
Source current (Body diode)	Continuous	ls	0.8	А
	Pulsed	Isp *1	8	А
Total power dissipation		P _D *2	1.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C
*1 Pw<10us Duty cycle<1%				

*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W
+ Mounted on a coromic board			

* Mounted on a ceramic board

Transistors

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	10	μA	Vgs=12V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	45	-	-	V	I _D = 1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V _{DS} = 45V, V _{GS} =0V	
Gate threshold voltage	VGS (th)	0.5	-	1.5	V	V _{DS} = 10V, I _D = 1mA	
Static drain-source on-state resistance		_	130	180	mΩ	I _D = 2.0A, V _{GS} = 4.5V	
	$R_{DS}(on)^*$	_	135	190	mΩ	I _D = 2.0A, V _{GS} = 4V	
		_	180	250	mΩ	I _D = 2.0A, V _{GS} = 2.5V	
Forward transfer admittance	Y _{fs} *	1.5	-	_	S	V _{DS} = 10V, I _D = 2.0A	
Input capacitance	Ciss	-	200	_	pF	V _{DS} = 10V	
Output capacitance	Coss	-	45	-	pF	Vgs=0V	
Reverse transfer capacitance	Crss	-	25	_	pF	f=1MHz	
Turn-on delay time	t _{d (on)} *	-	11	_	ns	Vdd≒25V	
Rise time	tr *	-	16	_	ns	$I_{D}=1.0A$	
Turn-off delay time	td (off) *	-	21	_	ns	- Vgs= 4.5V - R∟=25Ω	
Fall time	t _f *	-	11	_	ns	$R_{G}=10\Omega$	
Total gate charge	Qg *	-	2.9	4.1	nC	V _{DD} ≒25V V _{GS} =4.5V	
Gate-source charge	Q _{gs} *	-	0.7	-	nC	ID=2.0A	
Gate-drain charge	Q _{gd} *	_	0.9	_	nC	RL=12.5Ω RG=10Ω	

•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	V	I _S = 0.8A, V _{GS} =0V

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